

**FACSIMILE TRANSMISSION**

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**OFFICIAL COMMUNICATION**

Applicant : Todd R. Abbott  
 Serial No. : 09/943,078  
 Filed: August 30, 2001  
 Title : SEMICONDUCTOR DAMASCENE TRENCH AND METHODS  
 THEREOF  
 Docket No. : MIO 0083 PA  
 Examiner : Erik J. Kielin  
 Art Unit : 2813  
 Confirm No.: 7688

**OFFICIAL COMMUNICATION****FAX RECEIVED**

JAN 7 - 2003

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8/A  
P. Weller  
1-24B**OFFICIAL AMENDMENT****OFFICIAL AMENDMENT****IN THE UNITED STATES PATENT AND TRADEMARK OFFICE****FAX RECEIVED****Application of****JAN 7 - 2003**

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Jan 7, 2003  
 Thomas E. Lees

46,867  
 Reg. No.

Assistant Commissioner for Patents  
 Washington, D.C. 20231

Sir:

**AMENDMENT**

This paper is being filed in response to the Office Action dated November 15, 2002 in the identified application, having a reply due date of February 15, 2003. Reconsideration is respectfully requested in light of the amendments and remarks below.

**IN THE SPECIFICATION**

Please replace the paragraph starting on page 12, line 29 with the following:

Further, where the conductive layer comprises a polysilicon, an optional silicide layer may be desirable. Referring to Fig. 12B, after the formation of the spacers 102 and further doping is performed to define the doped source/drain regions 96, the silicide layer 71 is deposited over the structure 10. For example, after cobalt is deposited and a subsequent anneal process is performed, CoSi<sub>x</sub> is formed on the polysilicon conductive layer 70 and active areas, including the doped source/drain regions 96. The silicide layer 71 serves to lower the resistance of the polysilicon conductive layer 70. Subsequent

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cont'd